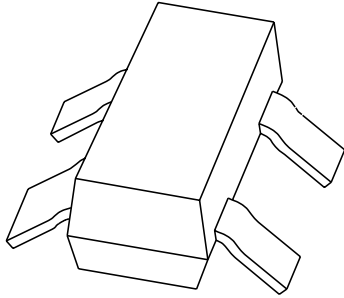


# DATA SHEET



## **BAS28** High-speed double diode

Product specification

# High-speed double diode

# BAS28

### FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA .

### APPLICATIONS

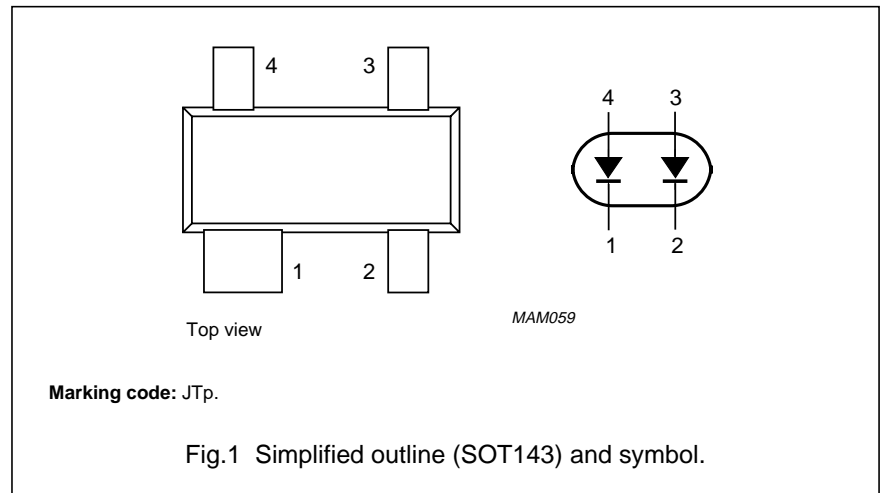
- High-speed switching in e.g. surface mounted circuits.

### DESCRIPTION

The BAS28 consists of two high-speed switching diodes, fabricated in planar technology, and encapsulated in the small plastic SMD SOT143 package. The diodes are not connected.

### PINNING

PIN	DESCRIPTION
1	cathode (k1)
2	cathode (k2)
3	anode (a2)
4	anode (a1)



### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{RRM}$	repetitive peak reverse voltage		–	85	V
$V_R$	continuous reverse voltage		–	75	V
$I_F$	continuous forward current	see Fig.2; note 1	–	215	mA
$I_{FRM}$	repetitive peak forward current		–	500	mA
$I_{FSM}$	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4 $t = 1\ \mu\text{s}$ $t = 1\ \text{ms}$ $t = 1\ \text{s}$	–	4 1 0.5	A A A
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$ ; note 1	–	250	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C

### Note

1. Device mounted on an FR4 printed-circuit board.

## High-speed double diode

## BAS28

**ELECTRICAL CHARACTERISTICS**

$T_j = 25\text{ °C}$ ; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_F$	forward voltage	see Fig.3			
		$I_F = 1\text{ mA}$	–	715	mV
		$I_F = 10\text{ mA}$	–	855	mV
		$I_F = 50\text{ mA}$	–	1	V
		$I_F = 150\text{ mA}$	–	1.25	V
$I_R$	reverse current	see Fig.5			
		$V_R = 25\text{ V}$	–	30	nA
		$V_R = 75\text{ V}$	–	1	$\mu\text{A}$
		$V_R = 25\text{ V}; T_j = 150\text{ °C}$	–	30	$\mu\text{A}$
		$V_R = 75\text{ V}; T_j = 150\text{ °C}$	–	50	$\mu\text{A}$
$C_d$	diode capacitance	$f = 1\text{ MHz}; V_R = 0$ ; see Fig.6	–	1.5	pF
$t_{rr}$	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$ ; $R_L = 100\ \Omega$ ; measured at $I_R = 1\text{ mA}$ ; see Fig.7	–	4	ns
$V_{fr}$	forward recovery voltage	when switched from $I_F = 10\text{ mA}$ ; $t_r = 20\text{ ns}$ ; see Fig.8	–	1.75	V

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		360	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

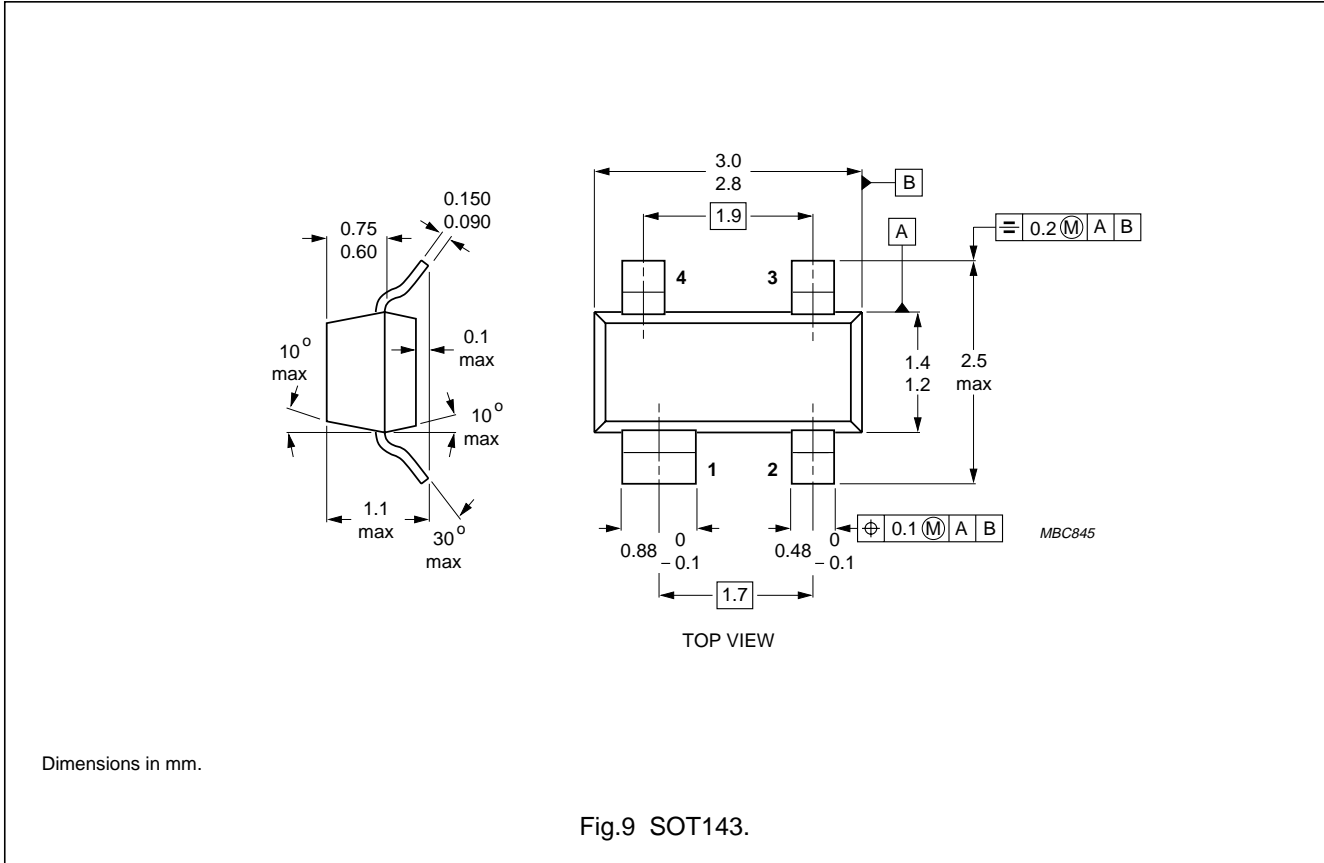
**Note**

1. Device mounted on an FR4 printed-circuit board.

High-speed double diode

BAS28

PACKAGE OUTLINE



DEFINITIONS

<b>Data Sheet Status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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